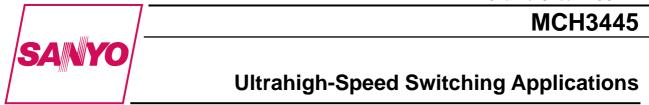
N-Channel Silicon MOSFET

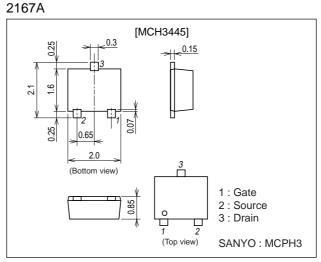


Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	۱D		2	A
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	8	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Symbol	Conditions	Ratings			1.114
		min	typ	max	Unit
V(BR)DSS	ID=1mA, VGS=0	20			V
IDSS	VDS=20V, VGS=0			1	μΑ
IGSS	V _{GS} =±8V, V _{DS} =0			±10	μΑ
VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
yfs	V _{DS} =10V, I _D =1A	1.4	2.4		S
R _{DS} (on)1	ID=1A, VGS=4V		125	165	mΩ
R _{DS} (on)2	ID=0.5A, VGS=2.5V		165	235	mΩ
RDS(on)3	ID=0.1A, VGS=1.8V		225	340	mΩ
	V(BR)DSS IDSS IGSS VGS(off) yfs RDS(on)1 RDS(on)2	V(BR)DSS ID=1mA, VGS=0 IDSS VDS=20V, VGS=0 IGSS VGS=±8V, VDS=0 VGS(off) VDS=10V, ID=1mA yfs VDS=10V, ID=1A RDS(on)1 ID=1A, VGS=4V RDS(on)2 ID=0.5A, VGS=2.5V	V(BR)DSS ID=1mA, VGS=0 20 IDSS VDS=20V, VGS=0 20 IGSS VGS=±8V, VDS=0 20 VGS(off) VDS=10V, ID=1mA 0.4 yfs VDS=10V, ID=1A 1.4 RDS(on)1 ID=1A, VGS=4V 20 RDS(on)2 ID=0.5A, VGS=2.5V 20	Symbol Conditions min typ V(BR)DSS ID=1mA, VGS=0 20 20 IDSS VDS=20V, VGS=0 20 20 IGSS VGS=±8V, VDS=0 20 20 VGS(off) VDS=10V, ID=1mA 0.4 2.4 I/yfs VDS=10V, ID=1A, VGS=4V 1.4 2.4 RDS(on)1 ID=1A, VGS=4V 125 165	Symbol Conditions min typ max V(BR)DSS ID=1mA, VGS=0 20 1 IDSS VDS=20V, VGS=0 20 1 IGSS VGS=±8V, VDS=0 1 ±10 VGS(off) VDS=10V, ID=1mA 0.4 1.3 yfs VDS=10V, ID=1A 1.4 2.4 RDS(on)1 ID=1A, VGS=4V 125 165 RDS(on)2 ID=0.5A, VGS=2.5V 165 235

Marking : ZW

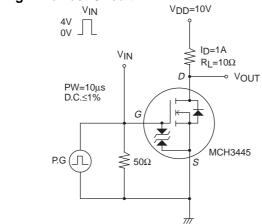
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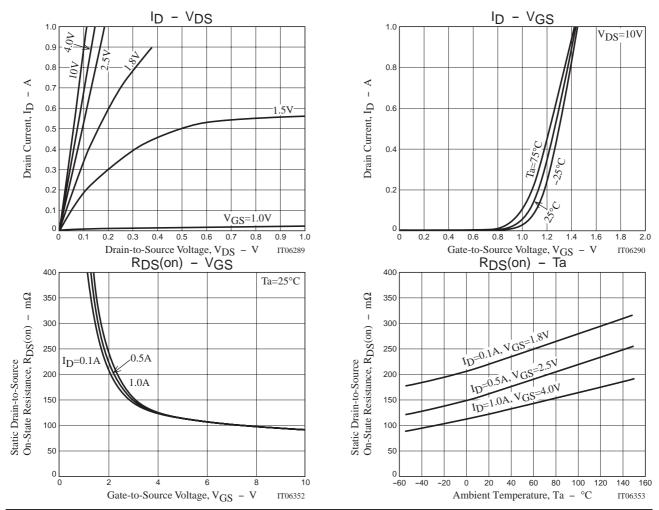
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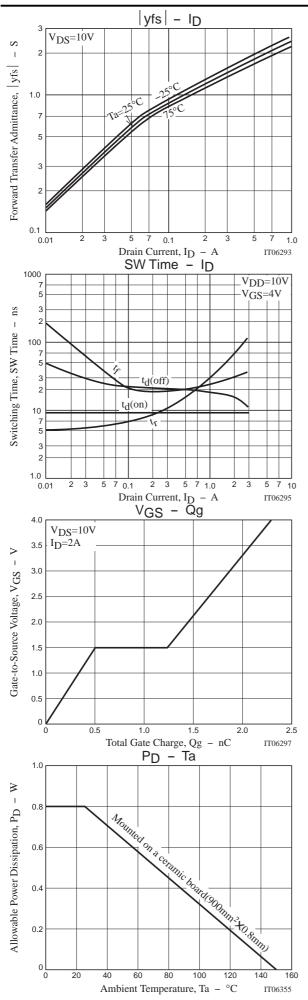
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

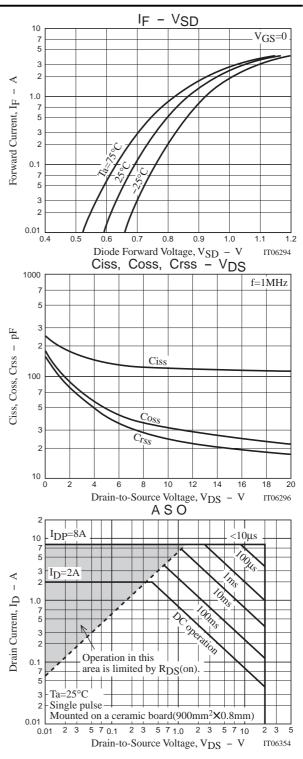
Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		120		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		31		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		25		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		9		ns
Rise Time	tr	See specified Test Circuit		29		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		18		ns
Fall Time	tf	See specified Test Circuit		22		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4V, I _D =2A		2.3		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4V, I _D =2A		0.50		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4V, I _D =2A		0.73		nC
Diode Forward Voltage	V _{SD}	IS=2A, VGS=0		0.94	1.2	V

Switching Time Test Circuit









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